High Voltage Transistors

PNP Silicon



ON Semiconductor[™]

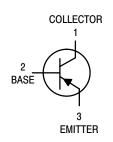
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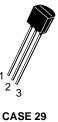
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC447 BC449, BC449A	VCEO	80 100	Vdc
Collector-Base Voltage BC447 BC449, BC449A	V _{CBO}	80 100	Vdc
Emitter-Base Voltage	VEBO	5.0	Vdc
Collector Current – Continuous	IC	300	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	TJ, T _{stg}	–55 to +150	°C
Moisture Sensitivity Level (MSL) Electrostatic Discharge (ESD)		MSL: 1 NA	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	200	°C/W
Thermal Resistance, Junction to Case	R _{θJC}	83.3	°C/W





TO-92 STYLE 17

MARKING DIAGRAM



BC44xx = Specific Device Code xx = 7, 9 or 9A Y = Year WW = Work Week

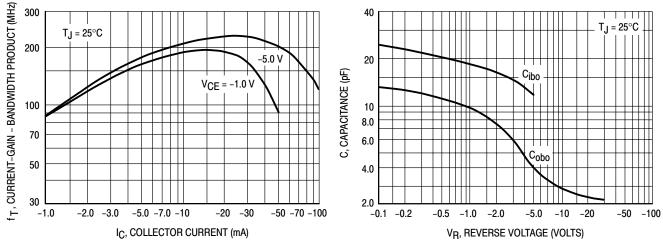
ORDERING INFORMATION

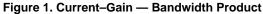
Device	Package	Shipping
BC447	TO-92	5000 Units/Box
BC449	TO-92	5000 Units/Box
BC449A	TO-92	5000 Units/Box

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		- 1 1			L	
Collector–Emitter Breakdown Voltage (Note 1.) ($I_C = 1.0$ mAdc, $I_B = 0$)	BC447 BC449, BC449A	V(BR)CEO	80 100			Vdc
Collector–Base Breakdown Voltage ($I_C = 100 \ \mu Adc, I_E = 0$)	BC447 BC449, BC449A	V(BR)CBO	80 100			Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \ \mu Adc, I_C = 0$)		V _{(BR)EBO}	5.0	_	_	Vdc
Collector Cutoff Current ($V_{CB} = 60 \text{ Vdc}, I_E = 0$) ($V_{CB} = 80 \text{ Vdc}, I_E = 0$)	BC447 BC449, BC449A	ICBO	-		100 100	nAdc
ON CHARACTERISTICS (Note 1.)						
DC Current Gain (I _C = 2.0 mAdc, V_{CE} = 5.0 Vdc) (I _C = 10 mAdc, V_{CE} = 5.0 Vdc) (I _C = 100 mAdc, V_{CE} = 5.0 Vdc)	BC447, BC449 BC449A BC447, BC449 BC447, BC449 BC447, BC449 BC447, BC449	hFE	50 120 50 100 50 60	- - - -	460 220 - - -	-
Collector–Emitter Saturation Voltage (I _C = 100 mAdc, I _B = 10 mAdc)		VCE(sat)	_	0.125	0.25	Vdc
Base–Emitter Saturation Voltage $(I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc})$		V _{BE(sat)}	_	0.85	-	Vdc
Base–Emitter On Voltage ($I_C = 2.0 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 100 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$) (Note 1.)		V _{BE(on)}	0.55 _	_ 0.76	0.7 1.2	Vdc
DYNAMIC CHARACTERISTICS		•			•	
Current–Gain – Bandwidth Product (I _C = 50 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)		ŕΤ	100	200	_	MHz

1. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle 2%







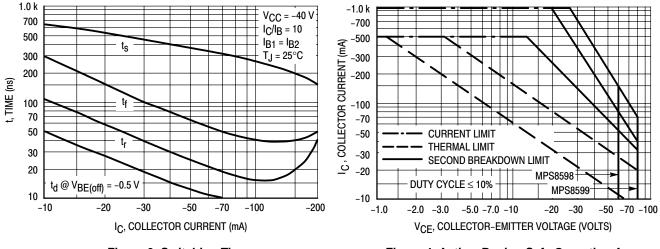
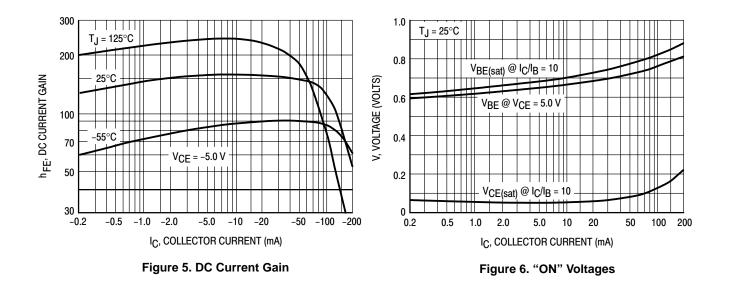
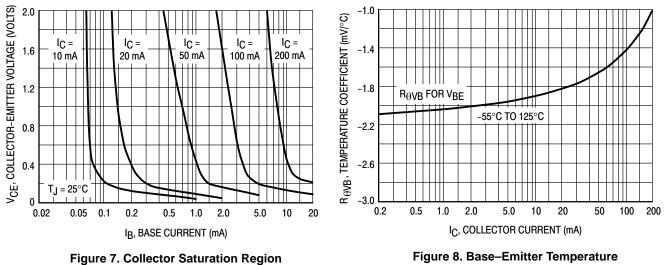




Figure 4. Active–Region Safe Operating Area





Coefficient

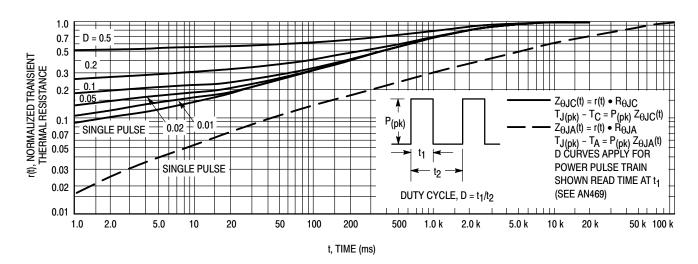
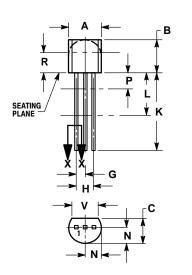


Figure 9. Thermal Response

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AL**





NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH. 3. CONTOUL OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
۷	0.135		3.43	

STYLE 17: PIN 1. COLLECTOR 2. BASE 3. EMITTER

<u>Notes</u>

<u>Notes</u>

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